

FDP090N10

N-Channel PowerTrench® MOSFET

100 V, 75 A, 9 mΩ

Features

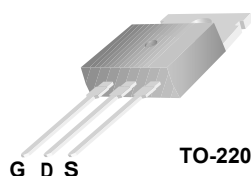
- $R_{DS(on)} = 7.2 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 75 \text{ A}$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

General Description

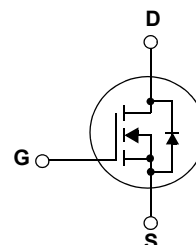
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter



TO-220



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted*

Symbol	Parameter		FDP090N10	Unit
V _{DSS}	Drain to Source Voltage		100	V
V _{GSS}	Gate to Source Voltage		±20	V
I _D	Drain Current	-Continuous (T _C = 85°C)	75	A
I _{DM}	Drain Current	- Pulsed (Note 1)	300	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		309	mJ
I _{AR}	Avalanche Current (Note 1)		75	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		20.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.6	V/ns
P _D	Power Dissipation	(T _C = 25°C)	208	W
		- Derate above 25°C	1.39	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP090N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.72	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP090N10	FDP090N10	TO-220	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$, $T_C = 25^\circ\text{C}$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.1	-	$V/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $T_C = 150^\circ\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 75\text{A}$	-	7.2	9	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 37.5\text{A}$	-	100	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	6185	8225	pF
C_{oss}	Output Capacitance		-	585	775	pF
C_{rss}	Reverse Transfer Capacitance		-	235	355	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 25\Omega$ (Note 4)	-	107	224	ns
t_r	Turn-On Rise Time		-	322	655	ns
$t_{d(off)}$	Turn-Off Delay Time		-	166	342	ns
t_f	Turn-Off Fall Time		-	149	309	ns
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 50\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$ (Note 4)	-	89	116	nC
Q_{gs}	Gate to Source Gate Charge		-	37	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	22	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	75	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	300	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 75A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 75A dI _F /dt = 100A/μs	-	73	-	ns
Q _{rr}	Reverse Recovery Charge		-	166	-	nC

Notes:

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: $L = 0.11\text{mH}$, $I_{AS} = 75\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- 3: $I_{SD} \leq 75\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
- 4: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

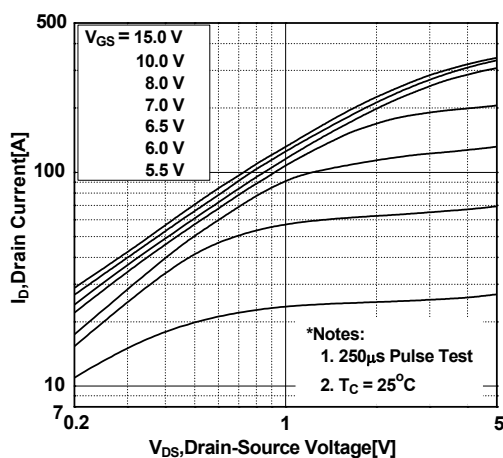


Figure 2. Transfer Characteristics

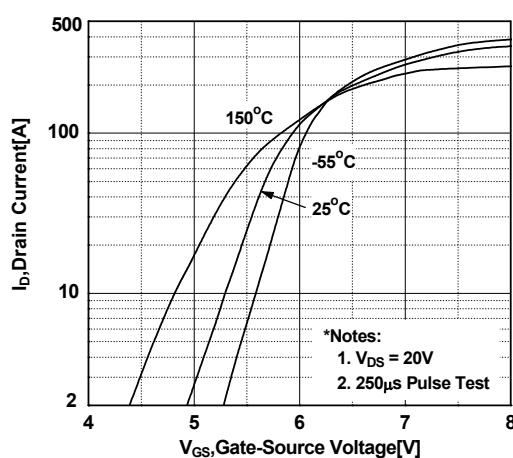


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

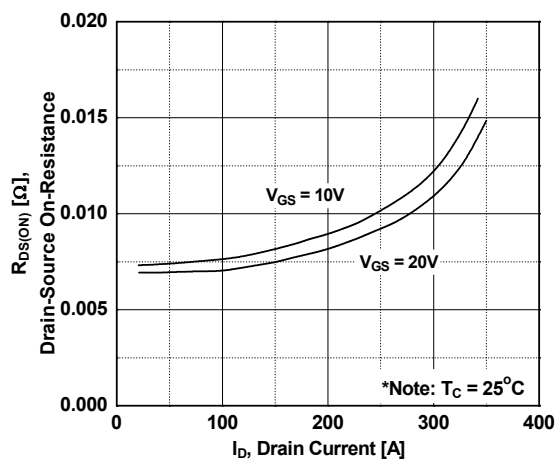


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

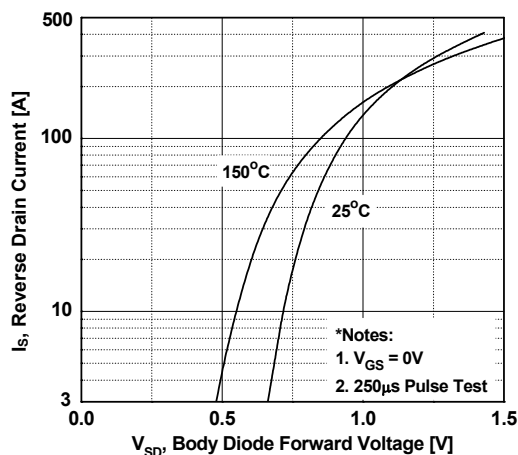


Figure 5. Capacitance Characteristics

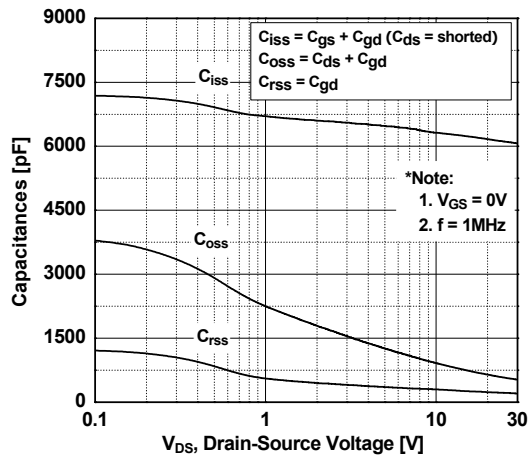
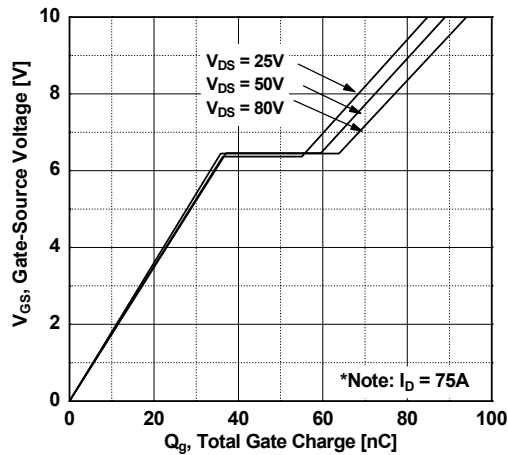


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

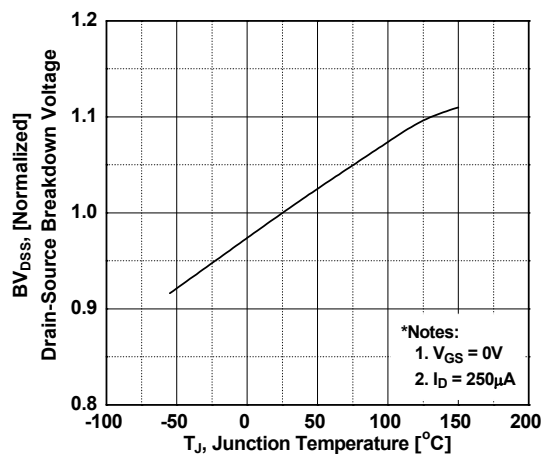


Figure 8. On-Resistance Variation vs. Temperature

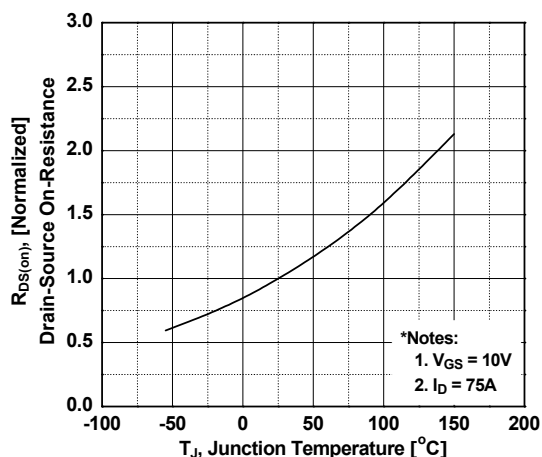


Figure 9. Maximum Safe Operating Area

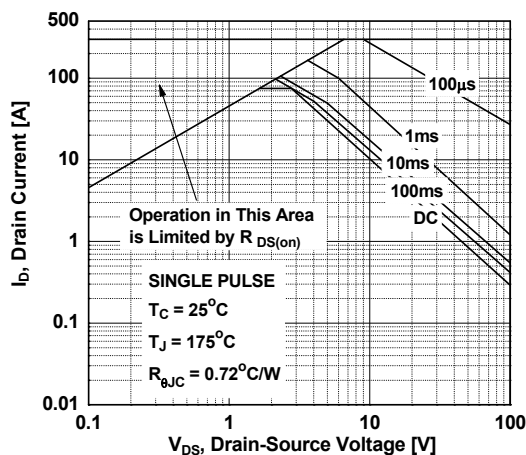


Figure 10. Maximum Drain Current vs. Case Temperature

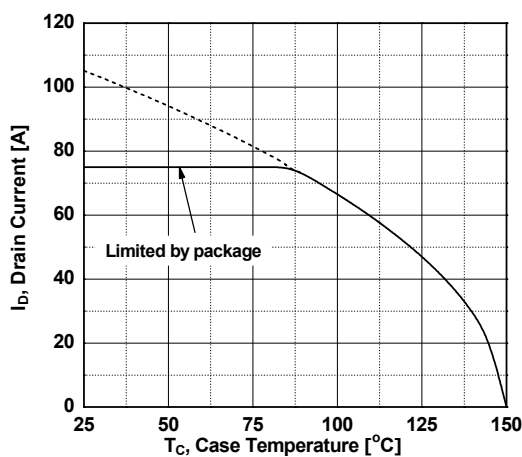
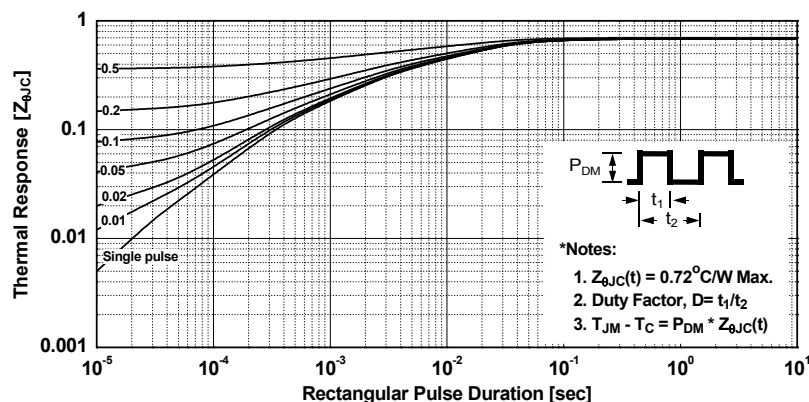
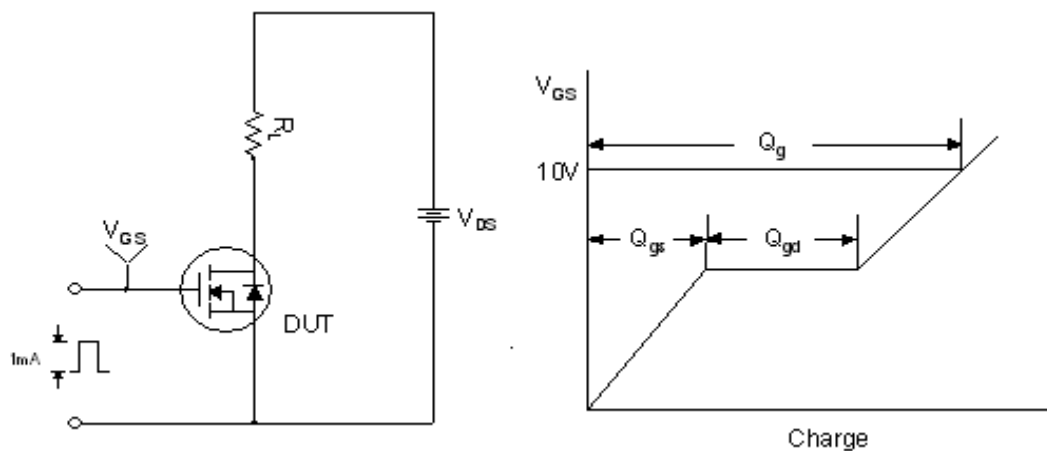


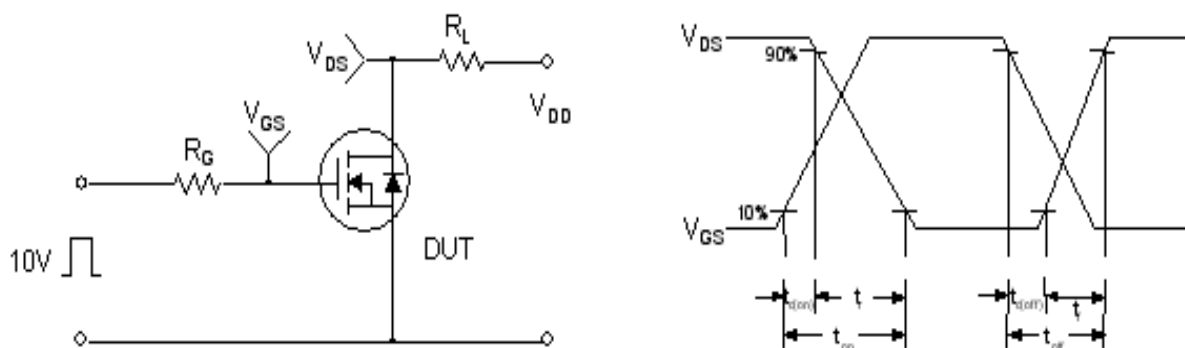
Figure 11. Transient Thermal Response Curve



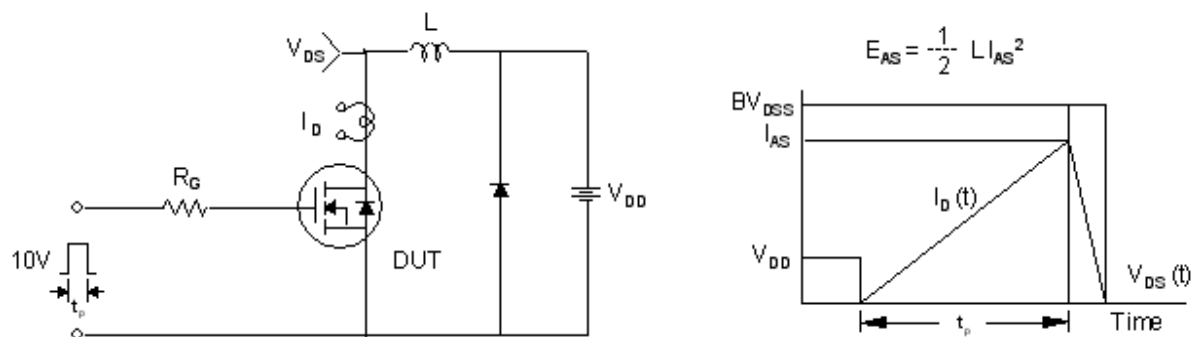
Gate Charge Test Circuit & Waveform



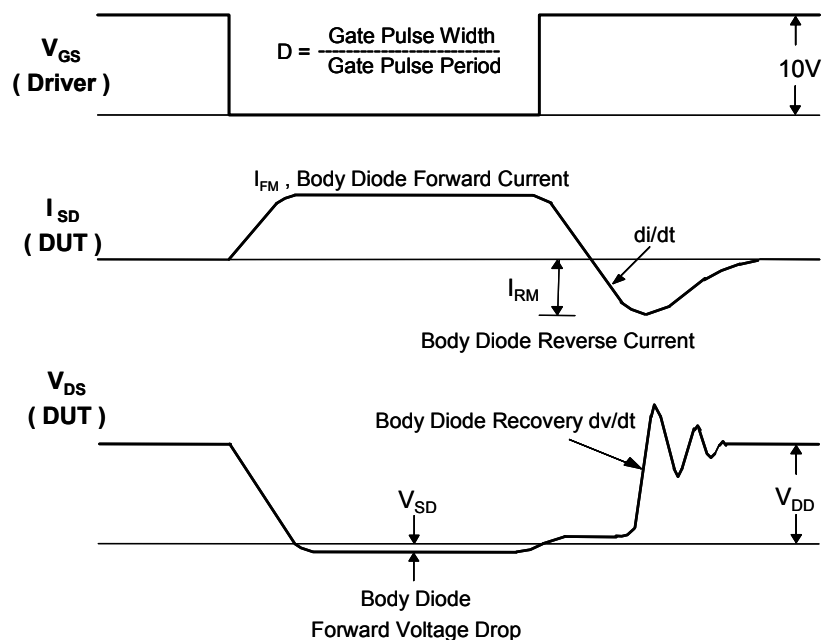
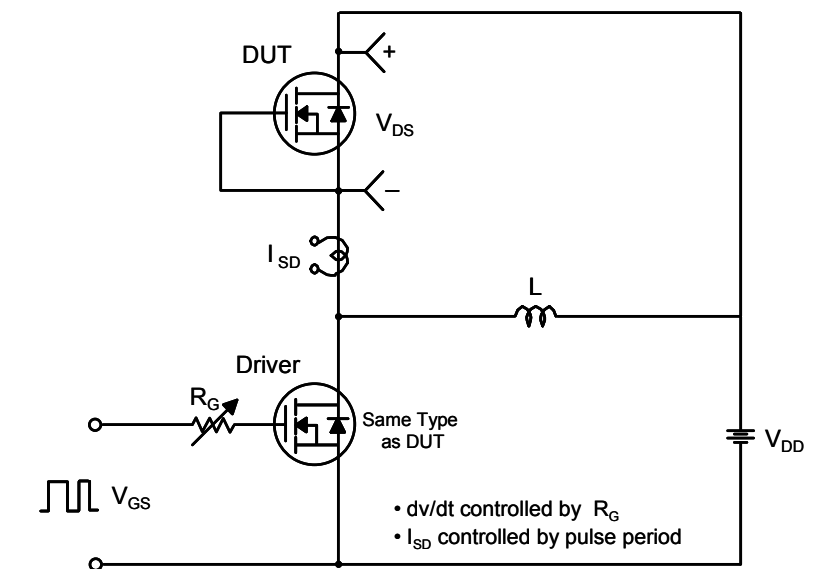
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

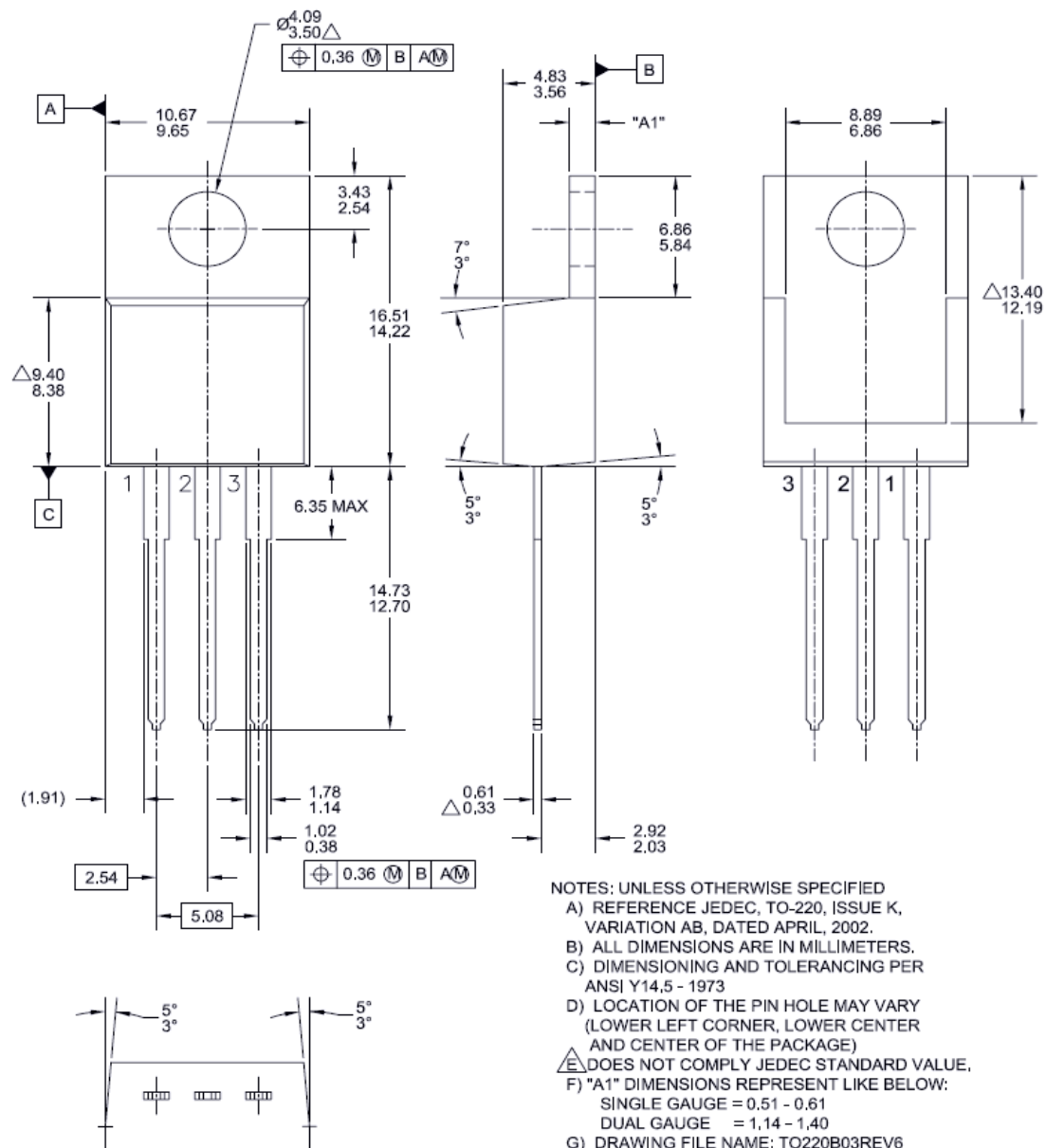


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-220B03





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.